

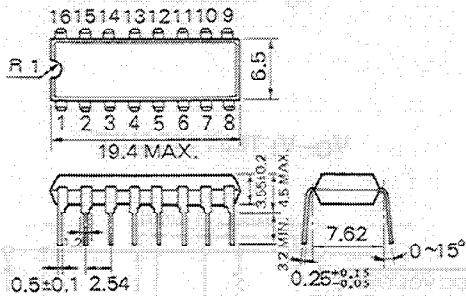
FLUORESCENT INDICATOR PANEL DRIVER
PNP-NPN SILICON EPITAXIAL TRANSISTOR ARRAY

DESCRIPTION

The μ PA80C is a monolithic array of seven PNP-NPN structured transistors. This device is especially suited for driving FIP (Fluorescent Indicator Panel).

PACKAGE DIMENSIONS

in millimeters



FEATURES

- High voltage rating V_{SS} : -60 V
- Pull down resistors incorporated
- Base current limiting resistors incorporated
- Package is 16 pin plastic DIP (Dual In-Line Package).

ABSOLUTE MAXIMUM RATINGS

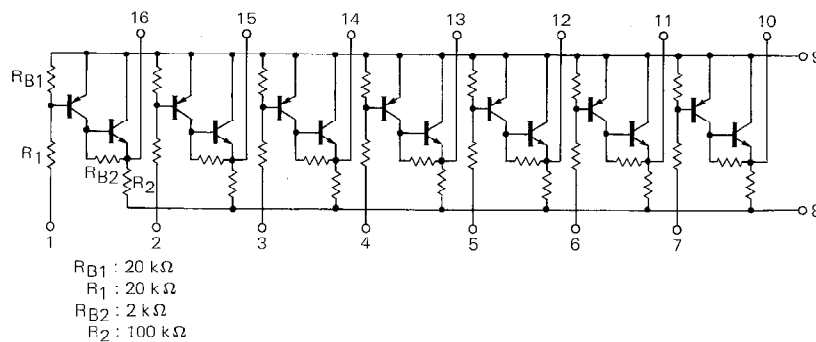
Maximum Voltages and Currents ($T_a=25^\circ\text{C}$)

Supply Voltage	V_{SS}	-60	V
Input Voltage	V_I	-20	V
Output Current	I_O	50	mA/unit
Maximum Power Dissipation			
Total Power Dissipation	P_d	550	mW
Maximum Temperature			
Storage Temperature	T_{stg}	-40 to +125	$^\circ\text{C}$
Operating Temperature	T_{opt}	-25 to +75	$^\circ\text{C}$

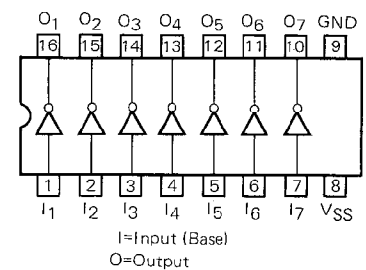
ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Output Leakage Current	I_L			1.0	μA	$V_{CE}=-50\text{ V}$
DC Current Gain	h_{FE1}	100	280			$V_{CE}=2.0\text{ V}, I_O=20\text{ mA}$
	h_{FE2}	250	450			$V_{CE}=2.0\text{ V}, I_O=40\text{ mA}$
Collector Saturation Voltage	$V_{CE(sat)}$		0.95	1.5	V	$I_O=20\text{ mA}, I_I=0.3\text{ mA}$
Input Current	I_I			1.0	mA	$V_I=-5.0\text{ V}$

EQUIVALENT CIRCUIT



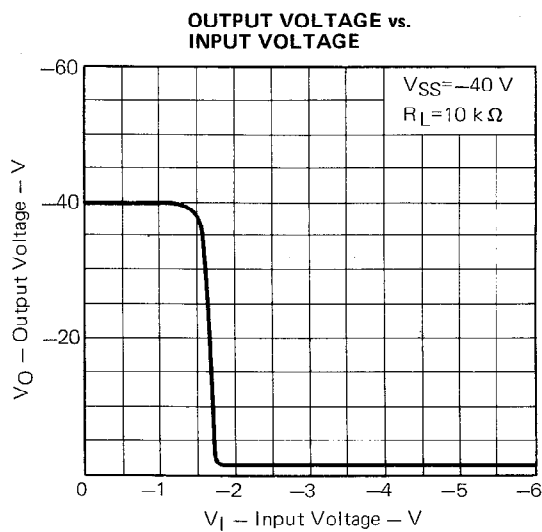
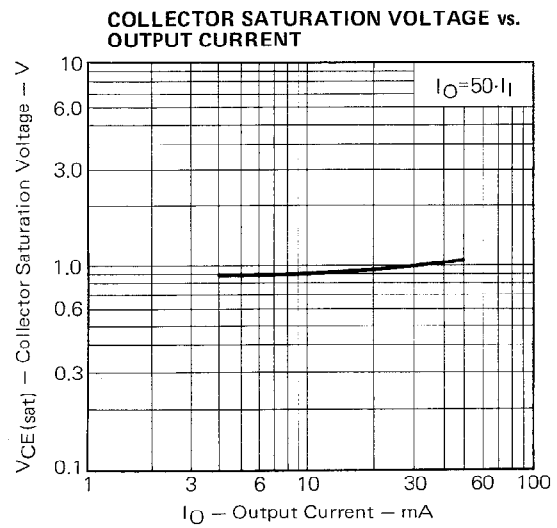
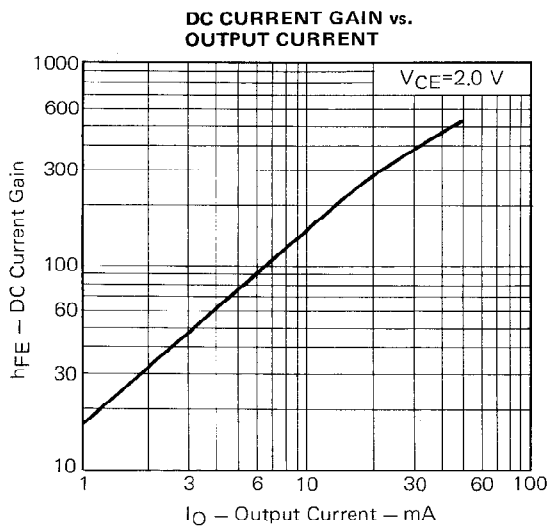
CONNECTION DIAGRAM (Top View)



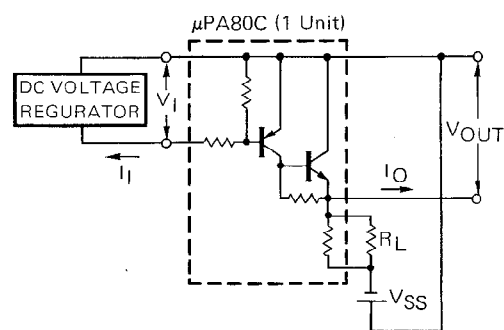
Nippon Electric Co., Ltd.

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TYPICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)



V_O-V_I TEST CIRCUIT



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